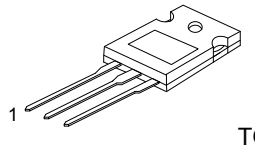
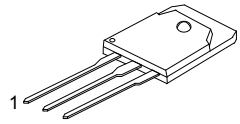
9N90

Power MOSFET

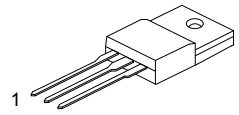
900V N-CHANNEL MOSFET



TO-247



TO-3P



TO-220F1

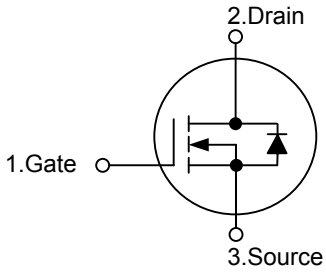
■ DESCRIPTION

The UTC **9N90** uses UTC's advanced proprietary, planar stripe, DMOS technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

■ FEATURES

* $R_{DS(ON)}$ = 1.4Ω @V_{GS} = 10 V
* Ultra Low Gate Charge (Typical 45 nC)
* Low Reverse Transfer Capacitance (C_{RSS} = Typical 14 pF)
* Fast Switching Capability
* Avalanche Energy Specified
* Improved dv/dt Capability, High Ruggedness

■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
9N90L-T47-T	9N90G-T47-T	TO-247	G	D	S	Tube
9N90L-T3P-T	9N90G-T3P-T	TO-3P	G	D	S	Tube
9N90L-TF1-T	9N90G-TF1-T	TO-220F1	G	D	S	Tube

9N90L-T47-T (1)Packing Type (2)Package Type (3)Lead Free	(1) T: Tube (2) T47: TO-247, T3P: TO-3P, TF1: TO-220F1 (3) G: Halogen Free, L: Lead Free

■ ABSOLUTE MAXIMUM RATING (T_C =25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	900	V
Gate-Source Voltage		V_{GSS}	±30	V
Continuous Drain Current (T_C = 25°C)		I_D	9.0	A
Pulsed Drain Current (Note 2)		I_{DM}	36	A
Avalanche Current (Note 2)		I_{AR}	9.0	A
Avalanche Energy	Single Pulsed(Note 3)	E_{AS}	900	mJ
	Repetitive(Note 2)	E_{AR}	28	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.0	V/ns
Power Dissipation	TO-247	P_D	160	W
	TO-3P		240	W
	TO-220F1		36	
Linear Derating Factor above T_C = 25°C	TO-247		1.28	W/°C
	TO-3P		2.22	W/°C
	TO-220F1		0.288	
Junction Temperature		T_J	150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating : Pulse width limited by maximum junction temperature
3. L = 21mH, I_{AS} = 9.0A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C
4. I_{SD}≤9.0A, di/dt ≤ 200A/μs, V_{DD}≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-247	θ_{JA}	50	°C/W
	TO-3P		40	°C/W
	TO-220F1		62.5	
Junction-to-Case	TO-247	θ_{JC}	0.78	°C/W
	TO-3P		0.52	°C/W
	TO-220F1		3.47	

■ ELECTRICAL CHARACTERISTICS (T_J =25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS} = 0 V, I_D = 250μA	900			V
Drain-Source Leakage Current		I_{DSS}	V_{DS} = 900 V, V_{GS} = 0 V			10	μA
Gate-Body Leakage Current	Forward	I_{GSSF}	V_{GS} = 30 V, V_{DS} = 0 V			100	nA
	Reverse	I_{GSSR}	V_{GS} = -30 V, V_{DS} = 0 V			-100	nA
Breakdown Voltage Temperature Coefficient		$\triangle BV_{DSS}/\triangle T_J$	I_D = 250μA, Referenced to 25°C		0.99		V/°C
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS} = V_{GS}, I_D = 250μA	3.0		5.0	V
Static Drain-Source On-Resistance		$R_{DS(ON)}$	V_{GS} = 10 V, I_D = 4.5 A		1.12	1.4	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz		2100	2730	pF
Output Capacitance		C_{OSS}			175	230	pF
Reverse Transfer Capacitance		C_{RSS}			14	18	pF

■ ELECTRICAL CHARACTERISTICS(Cont.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{D(ON)}$	V_{DD} = 450V, I_D =11.0 A, R_G = 25Ω (Note 1, 2)		50	110	ns
Turn-On Rise Time	t_R			120	250	ns
Turn-Off Delay Time	$t_{D(OFF)}$			100	210	ns
Turn-Off Fall Time	t_F			75	160	ns
Total Gate Charge	Q_G	V_{DS} = 720V, I_D = 11.0A, V_{GS} = 10 V (Note 1,2)		45	58	nC
Gate-Source Charge	Q_{GS}			13		nC
Gate-Drain Charge	Q_{GD}			18		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Drain-Source Diode Forward Voltage	V_{SD}	V_{GS} = 0 V, I_S = 9.0 A			1.4	V
Maximum Continuous Drain-Source Diode Forward Current	I_S				9.0	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				36	A
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, I_S = 9.0 A, d_{IF} / dt = 100 A/μs (Note 1)		550		ns
Reverse Recovery Charge	Q_{RR}			6.5		μC

Notes: 1. Pulse Test : Pulse width≤300μs, Duty cycle≤2%
2. Essentially independent of operating temperature

■ TEST CIRCUIT

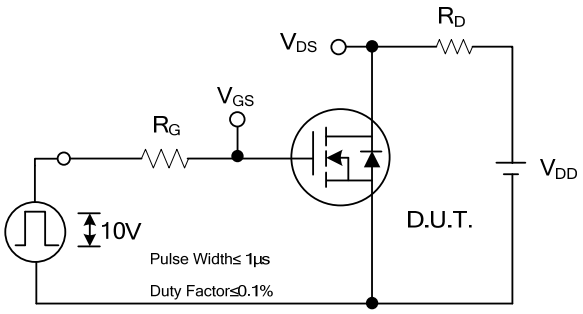


Fig. 2A Switching Test Circuit

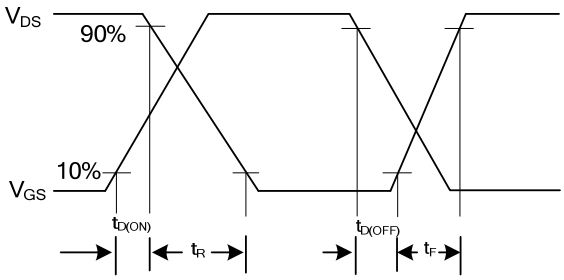


Fig. 2B Switching Waveforms

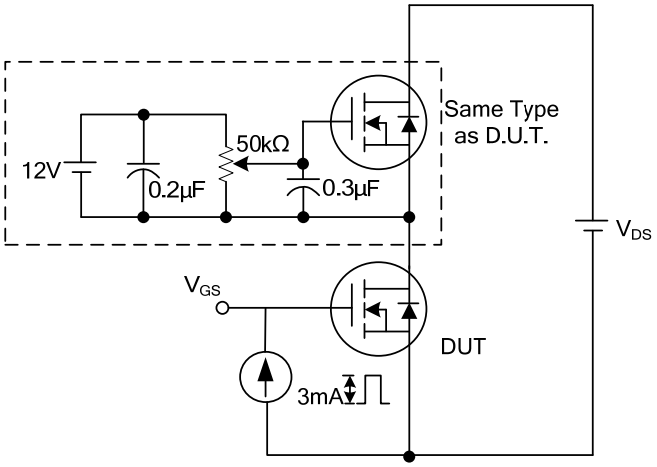


Fig. 3A Gate Charge Test Circuit

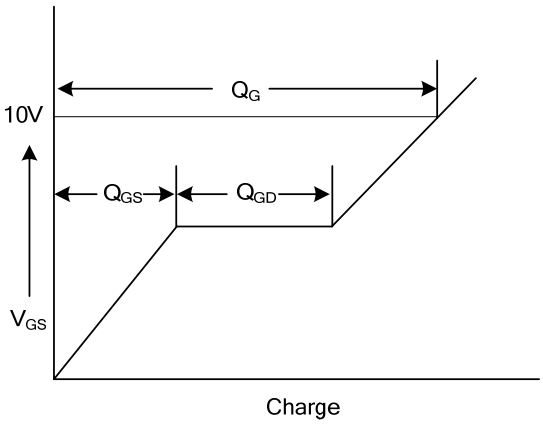


Fig. 3B Gate Charge Waveform

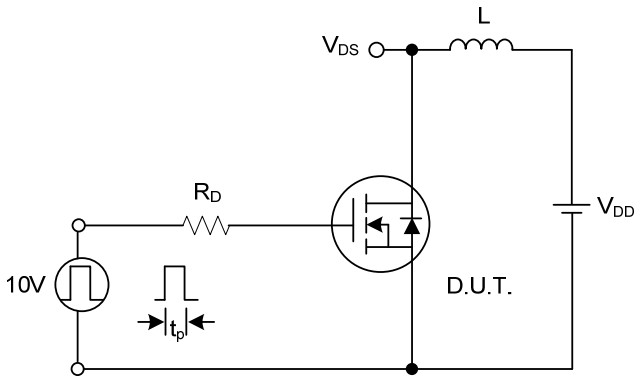


Fig. 4A Unclamped Inductive Switching Test Circuit

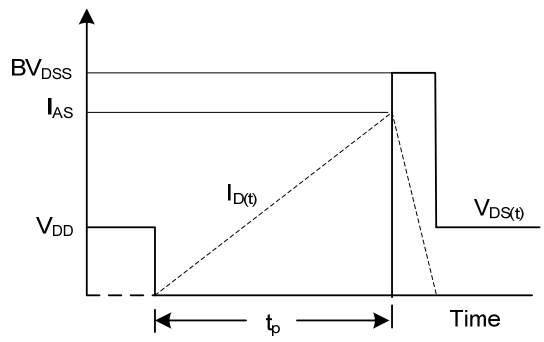


Fig. 4B Unclamped Inductive Switching Waveforms

■ TEST CIRCUIT(Cont.)

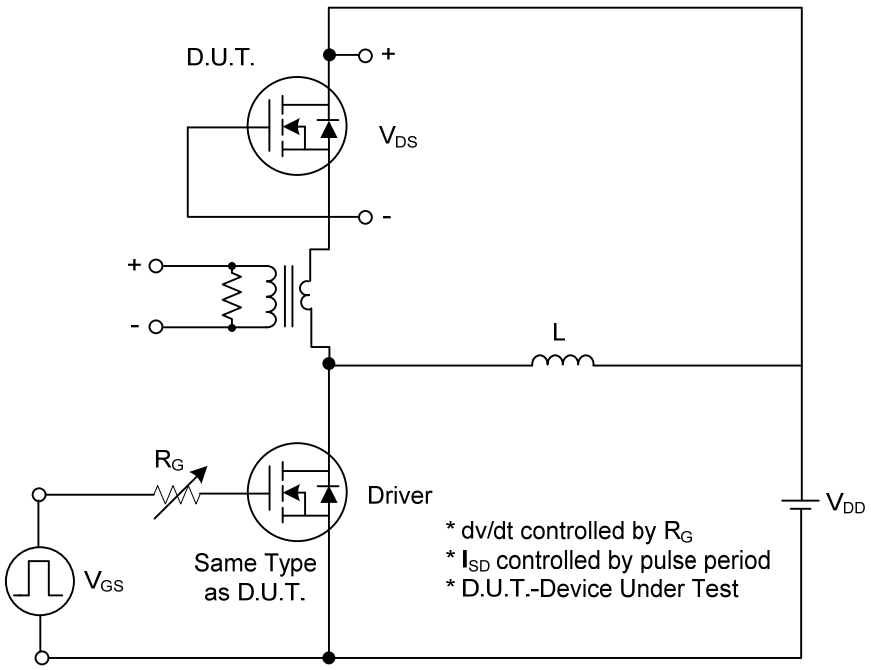
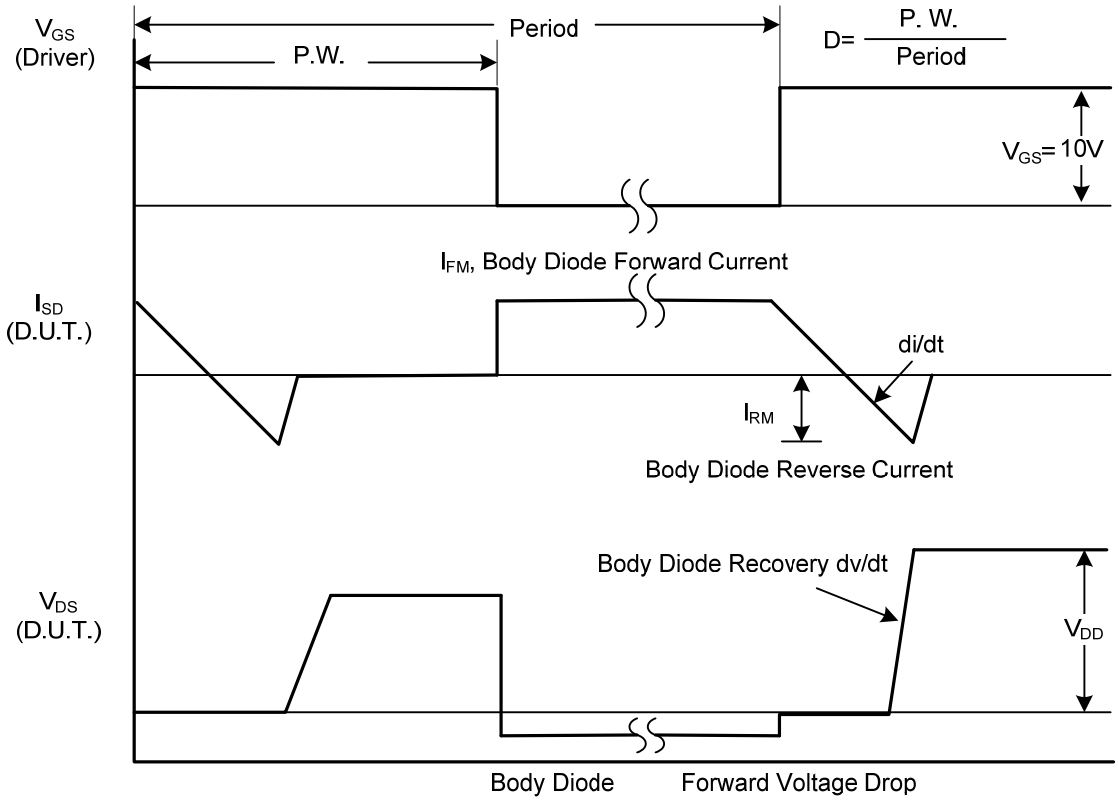
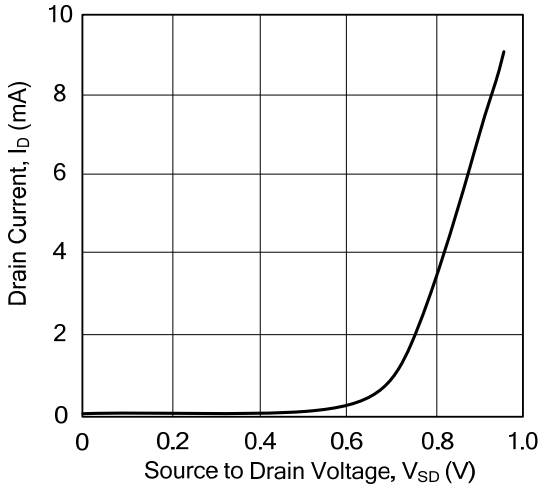


Fig. 1A Peak Diode Recovery dv/dt Test Circuit

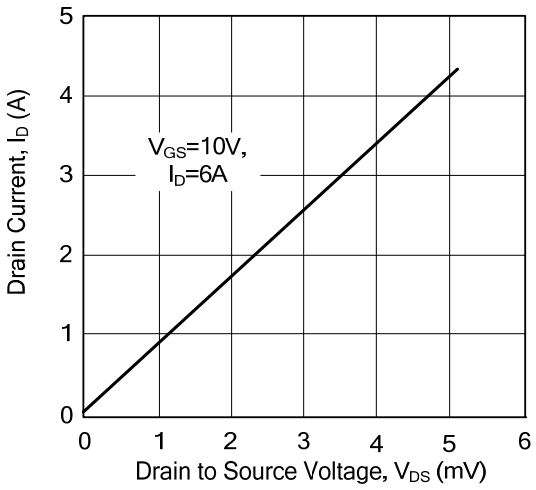


■ TYPICAL CHARACTERISTICS

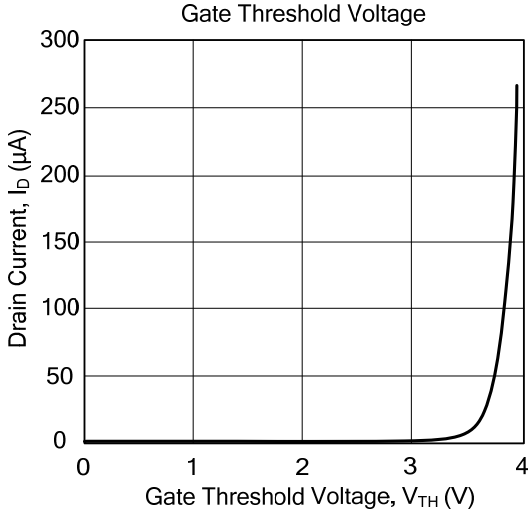
Drain Current vs.
Source to Drain Voltage



Drain-Source
On-State Resistance Characteristics



Drain Current vs.
Gate Threshold Voltage



Drain Current vs.
Drain-Source Breakdown Voltage